Abstracts

Accuracy Improvements in Two-Port Noise Parameter Extraction Method

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A. Boudiaf, M. Laporte, J. Dangla and G. Vernet. "Accuracy Improvements in Two-Port Noise Parameter Extraction Method." 1992 MTT-S International Microwave Symposium Digest 92.3 (1992 Vol. III [MWSYM]): 1569-1572.

The 4 transistor noise parameters extraction method based on the measurement of the device noise figure for more than 4 source reflection coefficients and the subsequent minimisation of a suitable error function, have been widely studied. But with the actual improvements in the field of the transistor noise performance (ex HEMT), and the increasing need of accuracy, aiming to obtain reliable models, it becomes necessary to evaluate the precision of the estimated noise parameters.

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